

60V N-Channel Power MOSFET

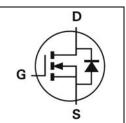
 V_{DSS} , 60V

 $R_{DS(ON)}$, 4.5m Ω (max.) @ V_Gs=10V $R_{DS(ON)}$, 5.5m Ω (max.) @ V_Gs=4.5V

 I_D , 100A







Description	Features
The SG60N03LD uses advanced Trench technology and designs to provide excellent $R_{\text{DS}(\text{ON})}$ with low gate charge. This device is suitable for use in PWM, load switching and general purpose applications.	 Low On-Resistance Low Input Capacitance Low Miller Charge Low Input / Output Leakage Pb-free lead plating; RoHS compliant
	Applications
	 Lithium-lon Secondary Batteries Load Switch DC-DC converters and Off-line UPS

Ordering Information

Ordering Code	RoHS Status	Package	Package Code	Packing	Quantity
SG60N03LD	Halogen-Free	TO-252	D	Tape & Reel	2,500

Absolute Maximum Ratings (T_A=25°C unless otherwise noted)

Parame	eter	Symbol	Value	Unit
Drain-Source Voltage		V _{DS}	60	V
Gate-Source Voltage		V _{GS}	±20	V
Drain Correct Continuous	T _C =25°C		100	А
Drain Current-Continuous	T _C =70°C	ID I	78	А
Drain Current-Pulsed Note 1	·	I _{DM}	450	А
Avalanche Current, L=0.5mH		las	26	А
Avalanche Energy, L=0.5mH		Eas	169	mJ
Maximum Dawar Dissination	T _C =25°C	D-	73	W
Maximum Power Dissipation	T _C =70°C	P _D	47	W
Storage Temperature Range		T _{STG}	-55 to +150	°C
Operating Junction Temperature Range		TJ	-55 to +150	°C

Thermal Resistance Ratings

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Maximum Junction-to-Ambient	R _{θJA}	Steady State	-	-	62	°C/W
Maximum Junction-to-Case	Rejc	Steady State	-	-	1.7	°C/W

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Electrical Characteristics (T_J=25°C unless otherwise noted)

OFF CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _{DS} =250µA	60	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =48V, V _{GS} =0V	-	-	1	μΑ
Gate-Body Leakage	Igss	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA

ON CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Gate Threshold Voltage	V _{GS(TH)}	V _{DS} =V _{GS} , I _{DS} =250µA	1.5	1.8	2.3	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _{DS} =20A	-	-	4.5	mΩ
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =4.5V, I _{DS} =10A	-	-	5.5	mΩ

DYNAMIC CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Input Capacitance	Ciss		-	3686	-	
Output Capacitance	Coss	V_{DS} =30V, V_{GS} =0V, f=1MHz	-	357	-	pF
Reverse Transfer Capacitance	Crss		-	124	-	

SWITCHING CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Turn-On Delay Time	T _{d(on)}		-	12	-	
Rise Time	t _r	V _{DS} =30V, I _D =20A, V _{GS} =10V,	-	4	-]
Turn-Off Delay Time	T _{d(off)}	D 00		50	-	ns
Fall Time	tf		-	6	-]
Total Gate Charge at 10V	Qg		-	50	-	
Gate to Source Gate Charge	Qgs	V _{DS} =30V, I _{DS} =20A, V _{GS} =10V	-	15	-	nC
Gate to Drain "Miller" Charge	Q _{gd}		-	2.5	-	

DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Drain-Source Diode Forward Voltage	V_{SD}	V _{GS} =0V, I _{DS} =1A	-	-	1.3	V
Body Diode Reverse Recovery Time	trr	L-204 dl/dt-1004/up	-	22	-	ns
Body Diode Reverse Recovery Charge	Qrr	I _F =20A, dl/dt=100A/μs	-	120	-	nC

Notes:

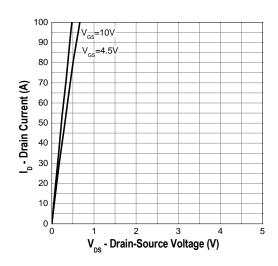
- 1. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2%.
- 2. R_{BJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R_{BJC} is guaranteed by design while R_{BJA} is determined by the user's board design. R_{BJA} shown below for single device operation on FR-4 in still air.



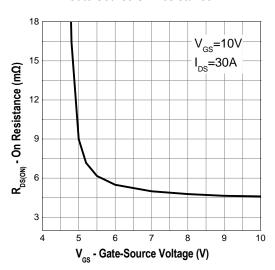
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Typical Operating Characteristics

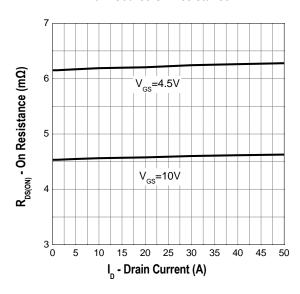
Output Characteristics



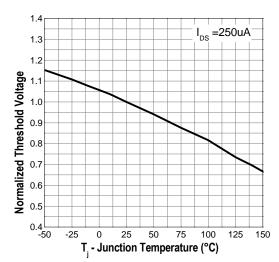
Gate-Source On Resistance



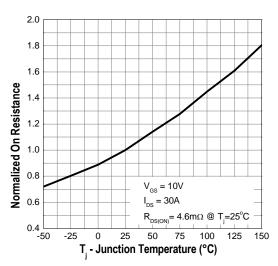
Drain-Source On Resistance



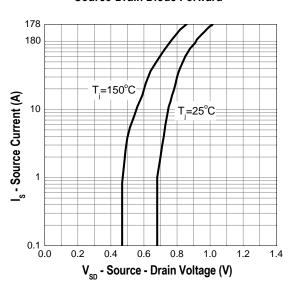
Gate Threshold Voltage



Drain-Source On Resistance



Source-Drain Diode Forward

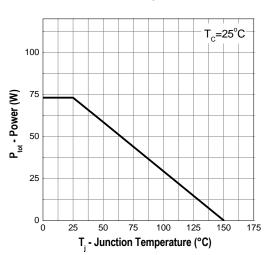




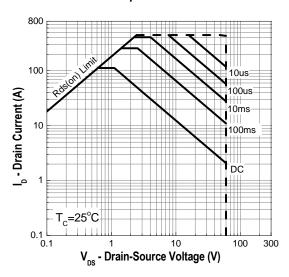
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Typical Operating Characteristics (Cont.)

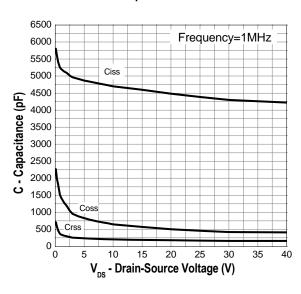
Power Dissipation



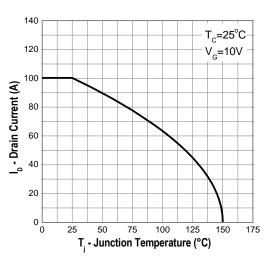
Safe Operation Area



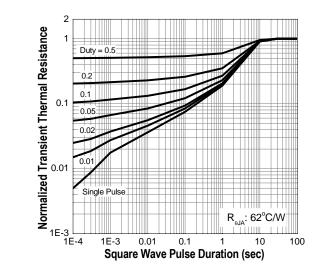
Capacitance



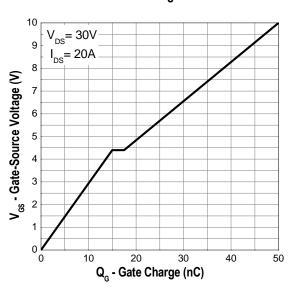
Drain Current



Transient Thermal Impedance



Gate Charge



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SG60N03LD
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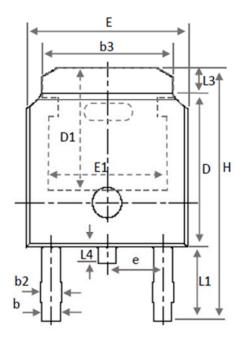
Marking Information

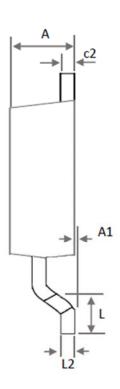
TO-252 (D)	Marking Rule
Laser Marking SG60N03LD YYMMXXX	Line 1 : Device Name SG60N03LD Line 2 : Date Code YYMMXXX YY : Year Code MM : Month Code XXX : Serial Number
Diagram	



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Package of Dimension





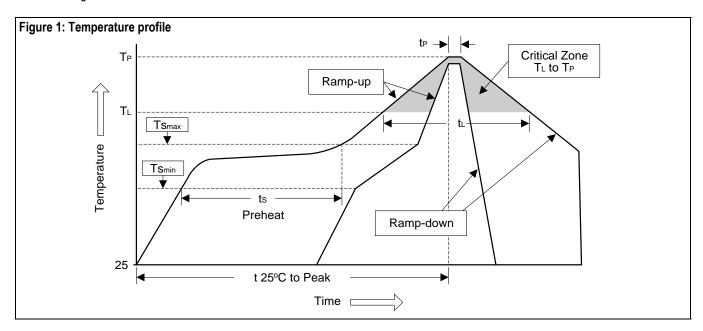
Symbol	Min	Nor	Max
E	6.35	6.54	6.731
L	1.40	1.59	1.78
L1		2.743 Ref	
L2		0.508 BS0	2
L3	0.89	1.08	1.27
L4	0.60	0.81	1.01
D	5.97	6.10	6.223
Н	9.40	9.91	10.41
b	0.64	0.77	0.89
b2	0.76	0.95	1.14
b3	4.95	5.21	5.46
е		2.286 BS0	2
Α	2.18	2.29	2.39
A1	0.00	0.07	0.13
c2	0.46	0.68	0.89
D1	5.21	-	-
E1	4.32	-	8



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Soldering Methods for Silicongear's Products

- 1. Storage environment: Temperature=10°C to 35°C Humidity=65%±15%
- 2. Reflow soldering of surface-mount devices



Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average ramp-up rate (T _L to T _P)	<3°C/sec	<3°C/sec
Preheat		
- Temperature Min (Ts _{min})	100°C	150°C
- Temperature Max (Ts _{max})	150°C	200°C
- Time (min to max) (ts)	60 to 120 sec	60 to 180 sec
Tsmax to T∟		
- Ramp-up Rate	<3°C/sec	<3°C/sec
Time maintained above:		
- Temperature (T∟)	183°C	217°C
- Time (t∟)	60 to 150 sec	60 to 150 sec
Peak Temperature (T _P)	240°C +0/-5°C	260°C +0/-5°C
Time within 5°C of actual Peak	10 to 30 sec	20 to 40 sec
Temperature (t₂)	10 to 50 sec	20 to 40 Sec
Ramp-down Rate	<6°C/sec	<6°C/sec
Time 25°C to Peak Temperature	<6 minutes	<8 minutes

3. Flow (wave) soldering (solder dipping)

Products	Peak Temperature	Dipping Time
Pb devices.	245°C ±5°C	5sec ±1sec
Pb-Free devices.	260°C +0/-5°C	5sec ±1sec



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